

A study of secondary particle production from carbon ion beam for radiotherapy

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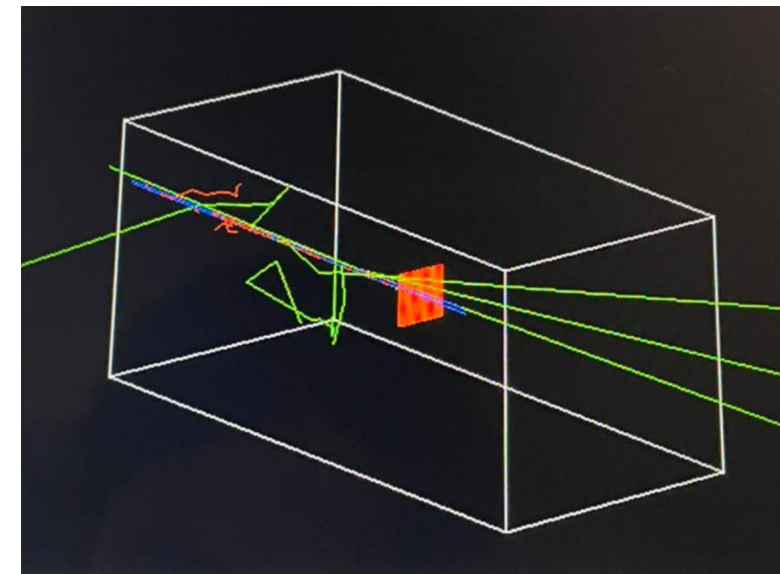
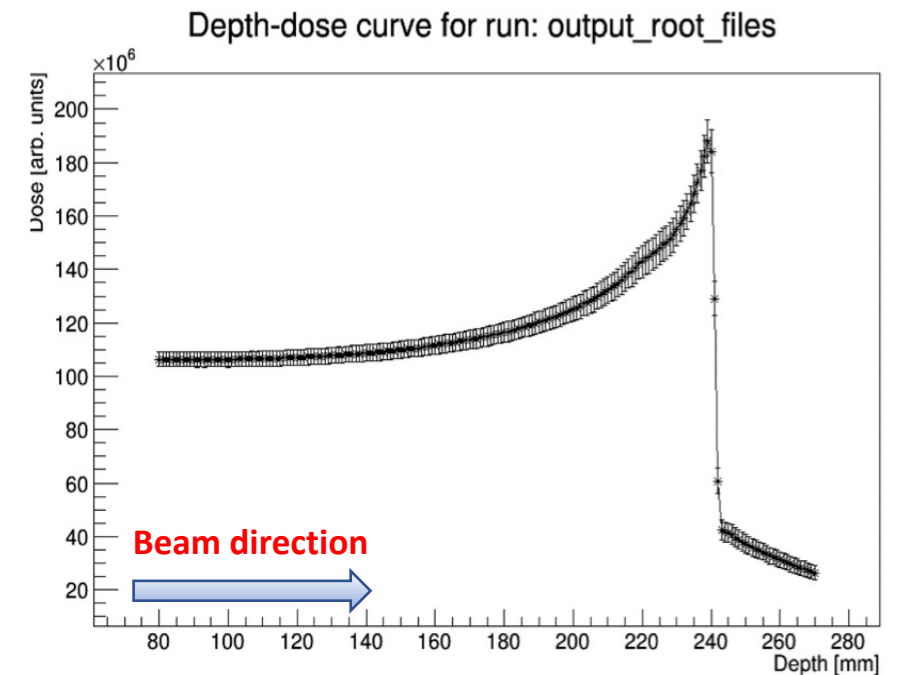
Department of Physics – High Energy Physics

Annual HEP meeting
May 19,2023 (Liverpool, UK)

Introduction

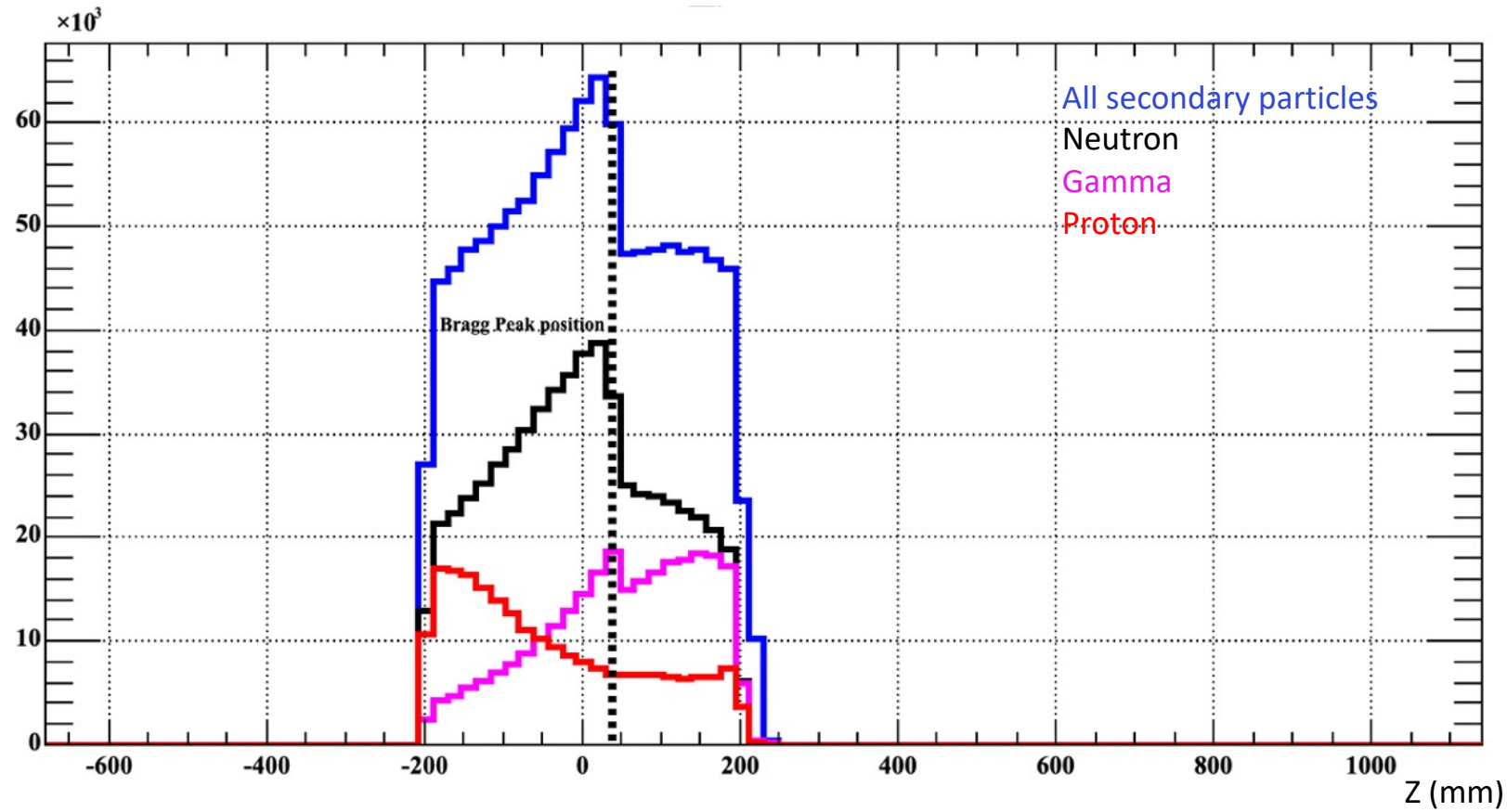
Research Aims:

- 1- Simulation study → monitor the primary beam → produced secondary radiation of hadron therapy (Carbon therapy) with water phantom, using Geant4 Monte Carlo software.
- 2- Secondary particle radiation → monitor the characteristics of the primary ion beam → measuring change particles coming out of the interactions between the ion beam and the molecules in the water.
- 3- Measurements → silicon pixel detectors such as a new HV-CMOS detector 'HVTrack' to compare with simulations.

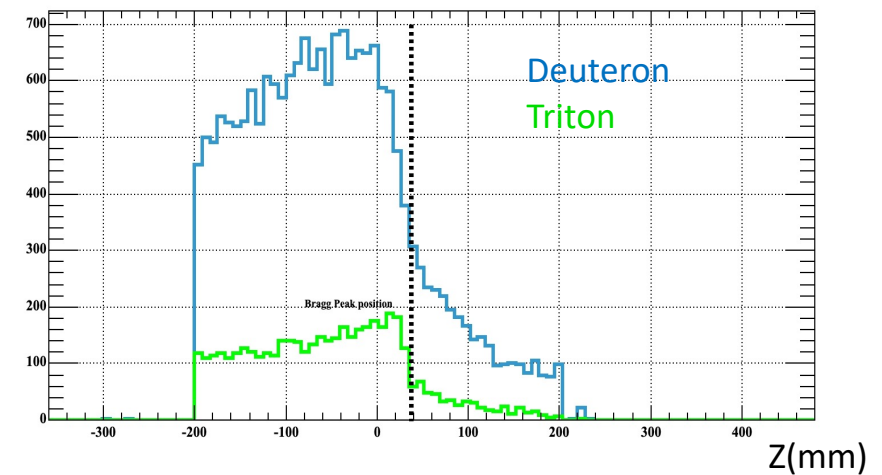


Geant4 snapshot shows the simulation where a carbon ion beam with energy 4.48 GeV is placed at 30 cm distance away from the water phantom. Silicon detectors are located inside the water.

Vertex of secondary particles



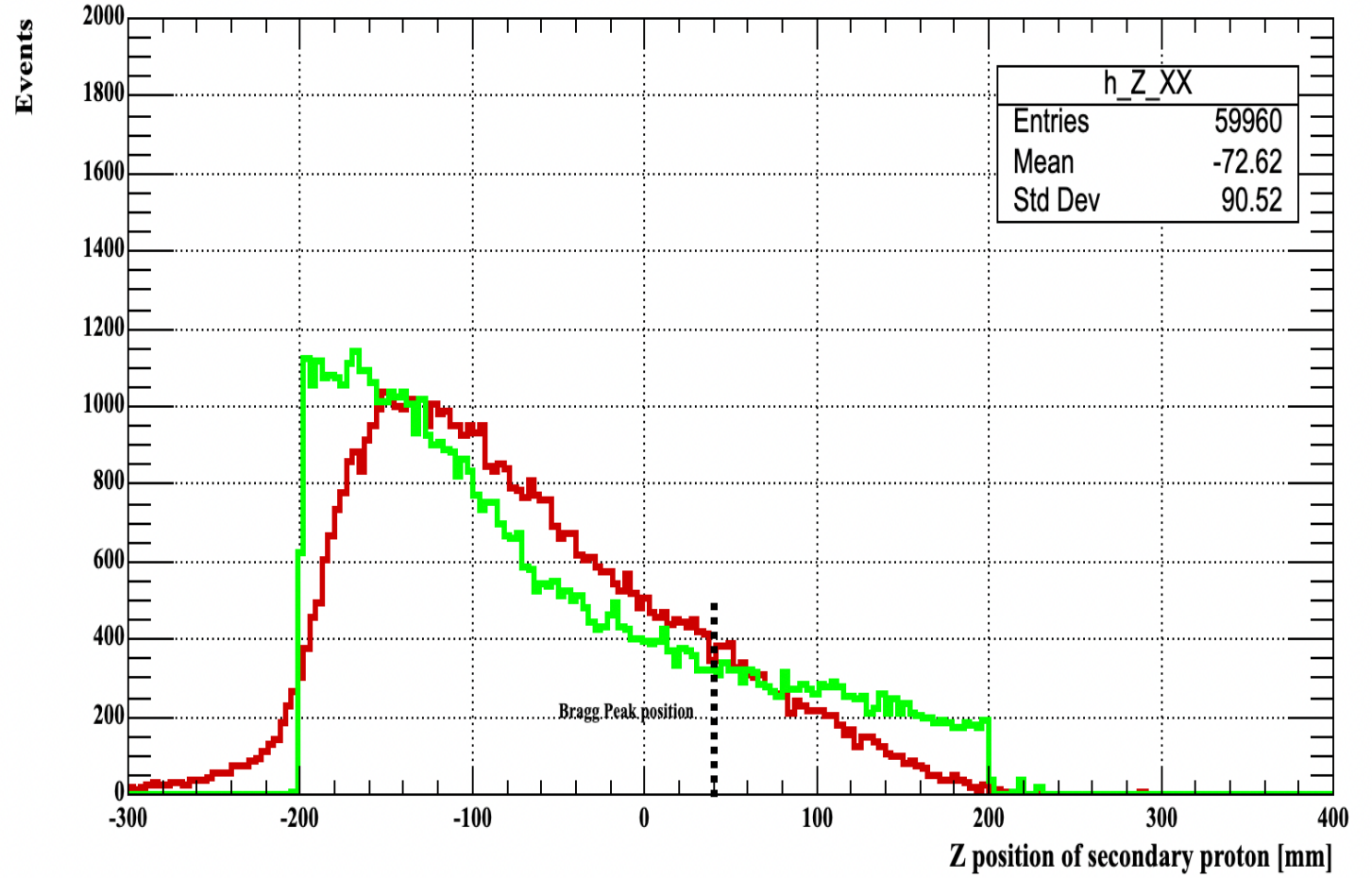
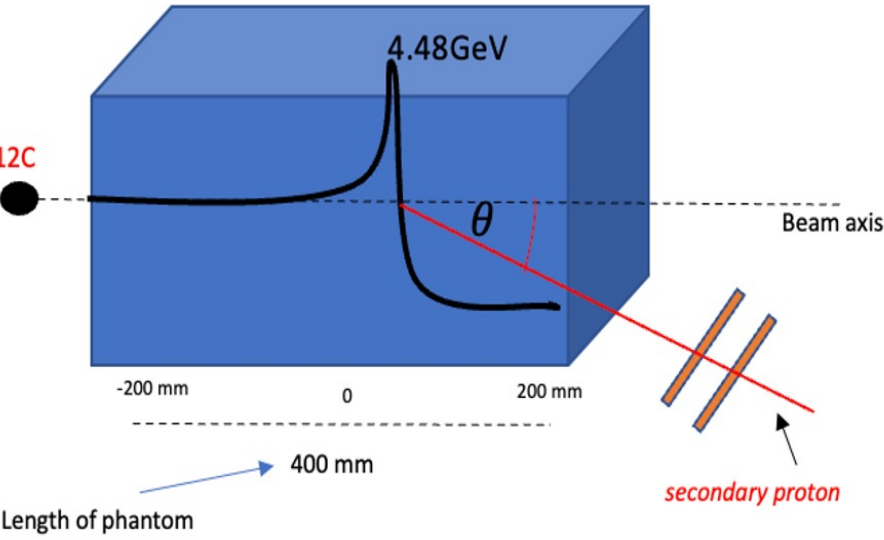
- The truth vertices of secondary particles corresponding to the Bragg Peak of 12C of 4.48 GeV with statistics 3M.



Geant4 toolkit version 10.03.
 Physics list: QGSP_BIC_HP.
 Beams: Carbon ion
 Energy: 4.48 GeV
 Event. no: 3M
 Medium: Water

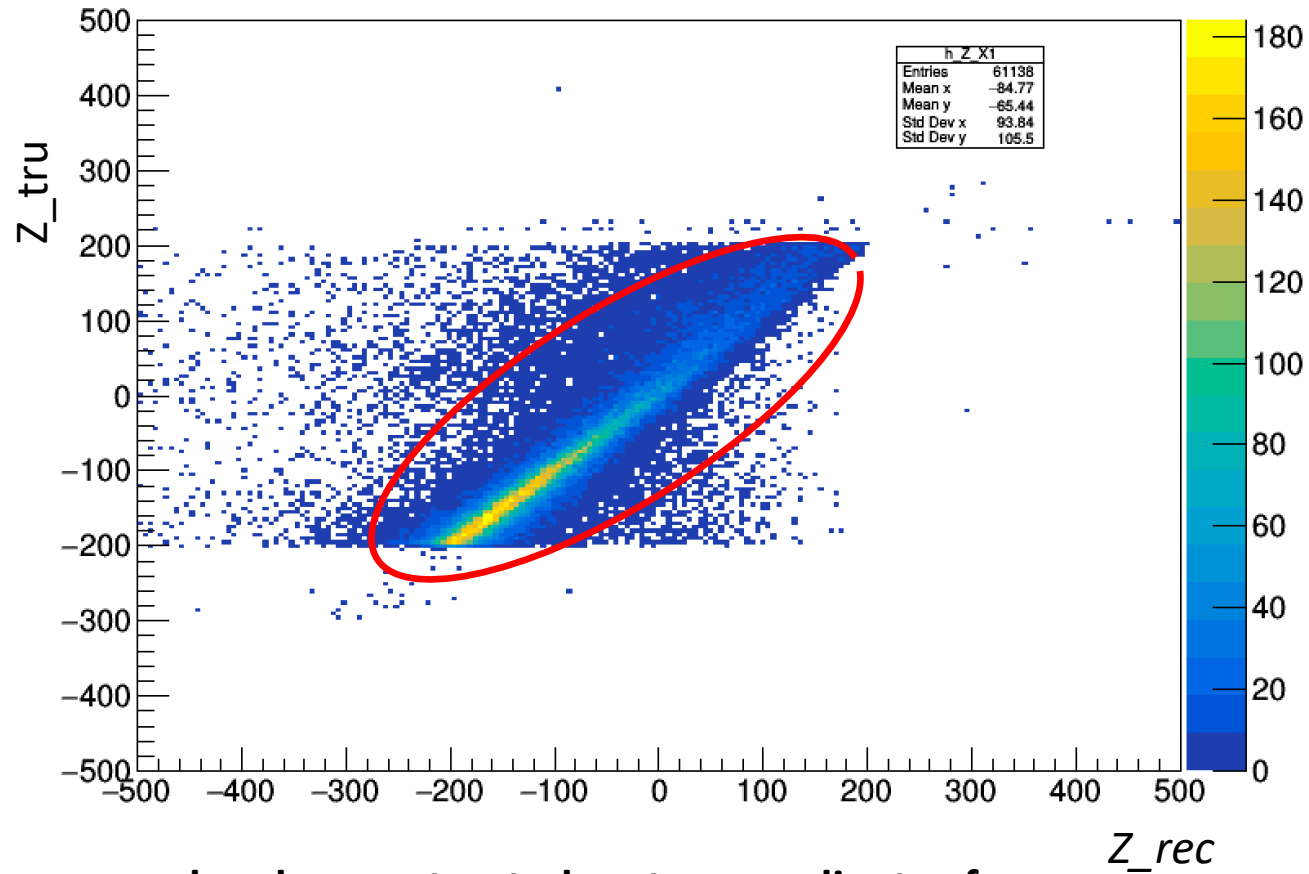
Secondary proton

$\theta = 35 \text{ deg}$



Z position of secondary proton as calculated from the positions in Si det
 truth Z positions of secondary proton

Correlation plot between real and reconstructed vertex coordinates for secondary protons along the beam direction



- Correlation plot between real and reconstructed vertex coordinates for secondary protons along the beam direction
- The correlation is linear
- One major factor which reduces the accuracy of the overall vertex distribution is straggling, where the trajectory of a secondary particle changes as it passes through the target before reaching the detector. This effect is more prominent for secondary particles of lower kinetic energy
- increasing linearly

Deposited Energy of secondary charged particles that is measured by using Si det

Geant4 toolkit version 10.03.

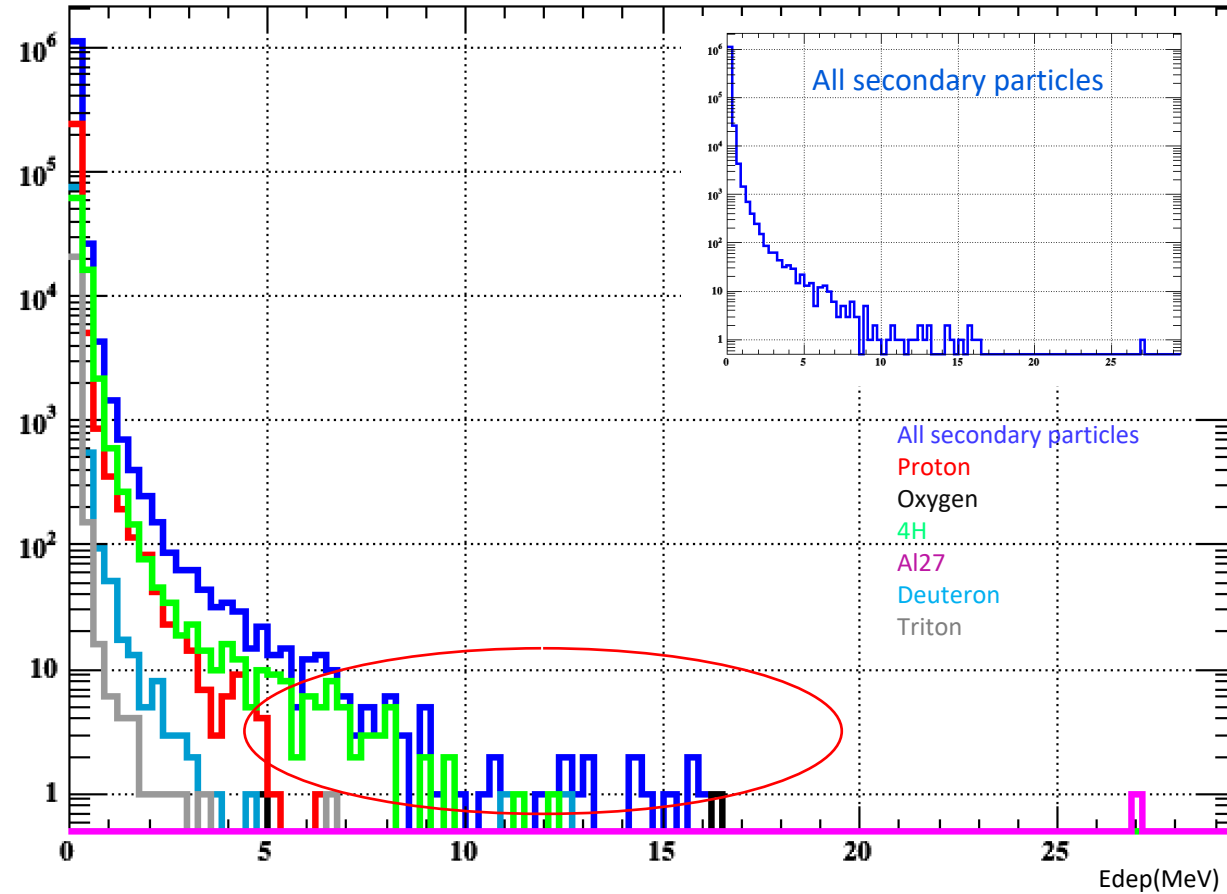
Physics list: QGSP_BIC_HP.

Beams: Carbon ion

Energy: 4.48 GeV

Event. no: 1M

Medium: Water



- **Energy deposition of secondary particles ~1-27 MeV**
- **Secondary ions produced during nuclear fragmentation processes**
- **The high energies deposition are generated by secondary ions**

Study the original positions and KE of gamma rays

Geant4 toolkit version 10.03.

Physics list: QGSP_BIC_HP.

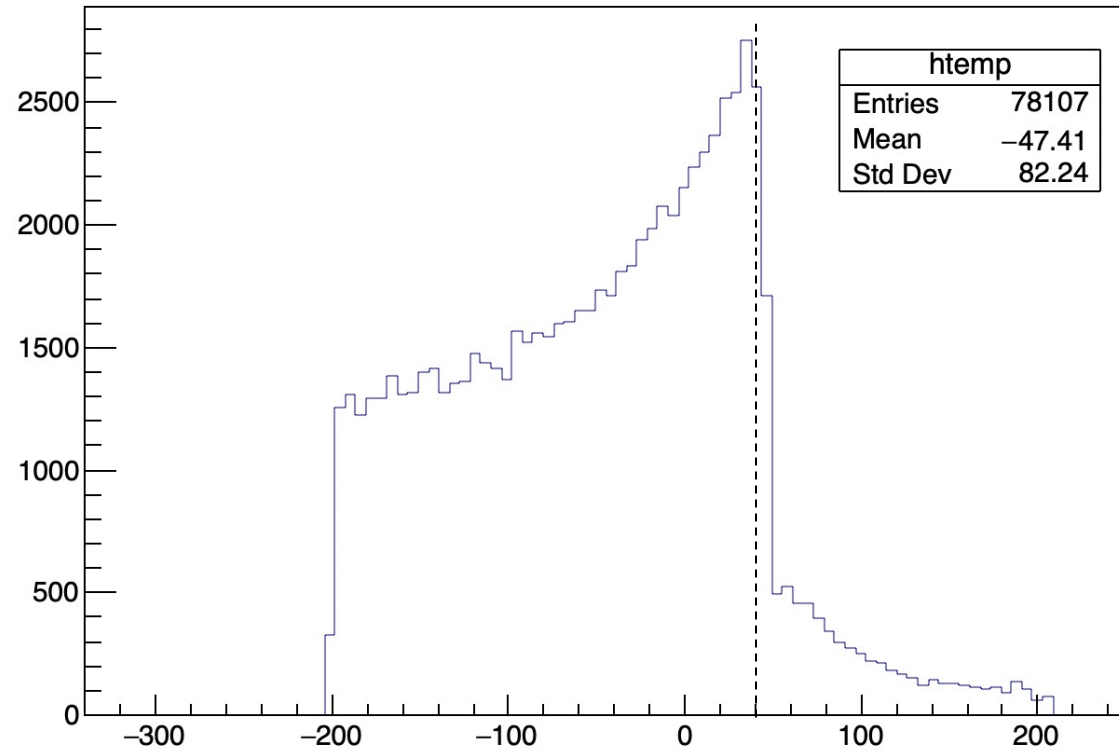
Beams: 12C

Energy: 4.48 GeV

Event. no: 800k

Medium: Water

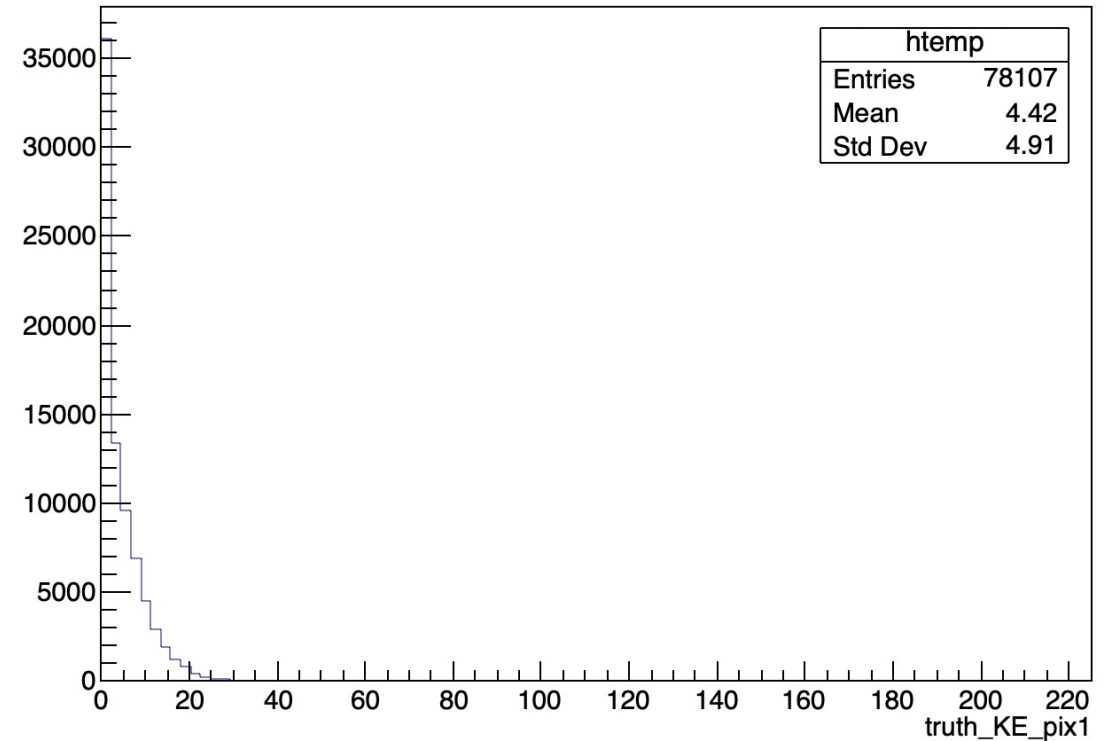
Thickness: 200 um



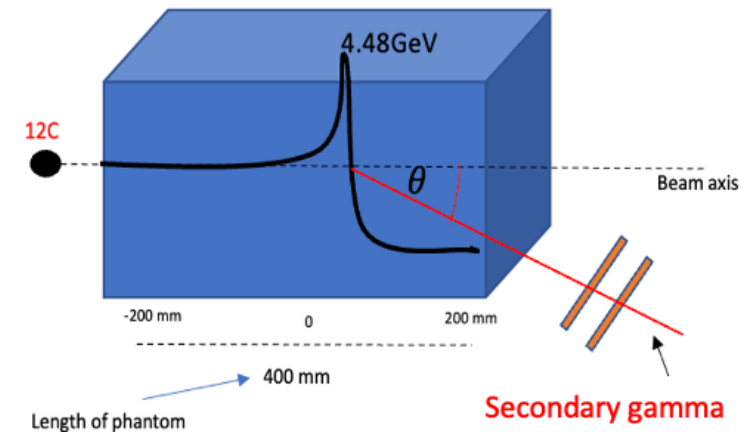
Original position of gamma rays that are produced from ion inelastic scattering (mm)

**dotted line represents bragg peak position*

**All original position of gamma rays that are produced from ion inelastic scattering are correlated to the beam range.*

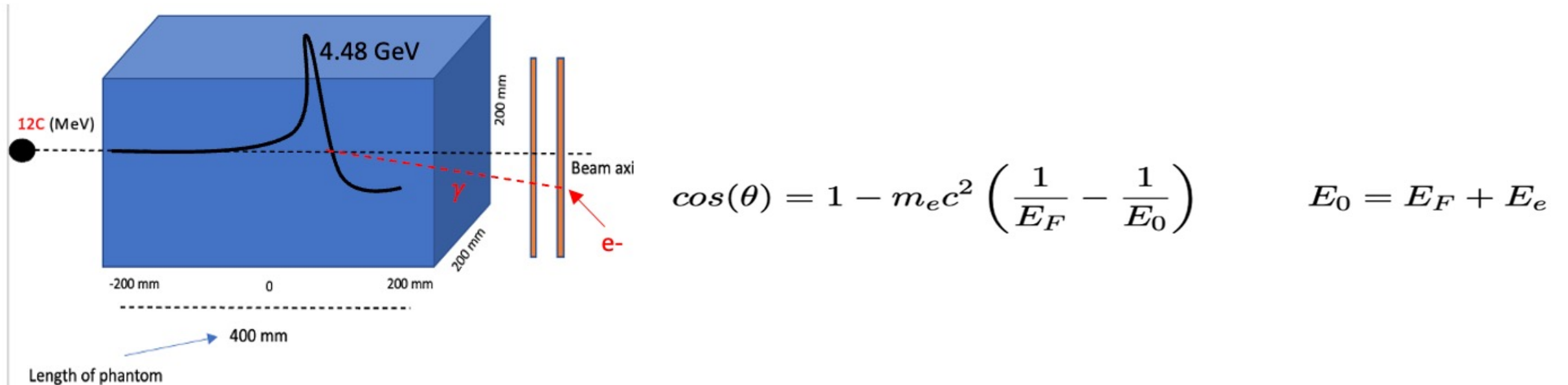


Mean KE of gamma rays that is produced from ion inelastic scattering (MeV)



Compton camera

A Compton camera is a promising γ -ray detector that operates in the wide energy range of a few tens of keV to MeV. The γ -ray detection method of a Compton camera is based on Compton scattering kinematics.

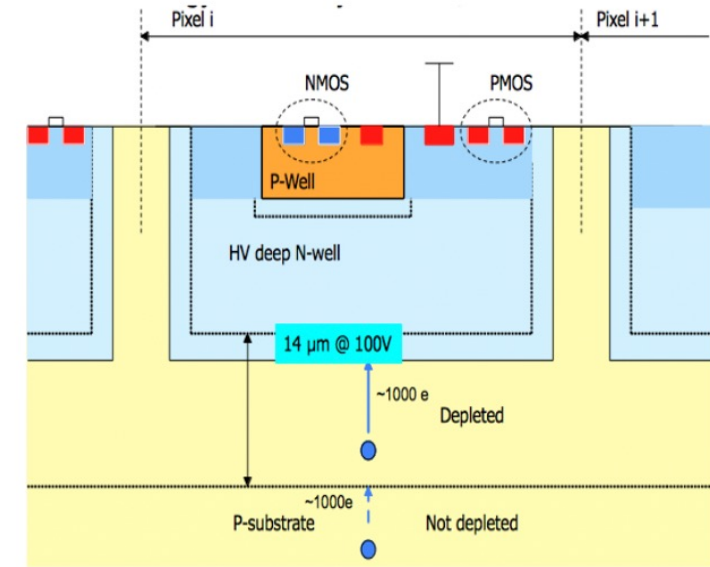


- We are aiming to simulate and measure gamma ray and subsequent scattered electron to track gamma or to identify where gamma was generated.
- we are looking into kinematic cuts that will allow us to predict the origins of the gamma ray hitting the first detector , by looking at the energy and position of the Compton scattered electron in the second detector.
- We will use a large area strip detector to measure scatter gamma ray in first detector and scattered electron in second detector.
- Measuring the scattered electron in the second detector is because the efficiency of measuring a double Compton scatter in 300um silicon is low and also because the Compton camera formula requires an energy measurement and the silicon will only give an energy loss measurement.

Semiconductor Tracking Detectors

HV-CMOS detector

- Readout and digitization electronics can be integrated on the same chip with the pixel array
- Very small pixel sizes are possible → high granularity
- Low mass detector giving less scattering
- Good speed and good radiation tolerance (HV-CMOS)



CMOS electronics placed inside the diode (inside the n-well)

V-CMOS

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Large area strip detector

- Large area strip detector (10x10cm) developed for the Dark Matter Particle Explorer (DAMPE) experiment
- 300μm thick sensors with a strip pitch of 242μm readout with VIKING ASIC.



~10x10cm DAMPE sensor with VIKING ASIC

Next Steps and Outlook

- **Doing measurements with silicon pixel detectors such as a new HV-CMOS detector 'HVTrack'.**
- **10x10cm thick silicon strip detector with 300um thick will be used as Compton Camera.**
- **Working on calculating the reconstruction of secondary gamma rays from Si (Compton Camera).**

Thank you!

Any questions?